# 2SD2321

### Silicon NPN epitaxial planar type

For low-frequency power amplification

#### Features

- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Satisfactory operation performances at high efficiency with the low-voltage power supply

	Unit: mm
+ 4.0±0.2 2.0±0.2	_
(0.8) 3 (0.6)	
0.75 max. []]) [] [] []	
<b>5.6</b>	0.1
<b>P</b>	5
0.45 <sup>+0.20</sup>	
	45 <sup>+0.20</sup>
	<u>:0.1</u>
	1 : Emitter
	2 : Collector
	3 : Base
<i>S</i> <sup>1</sup>	NS-B1 Package

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol Rating		Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	40	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	20	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	7	V	
Collector current	I <sub>C</sub>	5	А	
Peak collector current	I <sub>CP</sub>	8	Α	
Collector power dissipation	P <sub>C</sub>	400	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

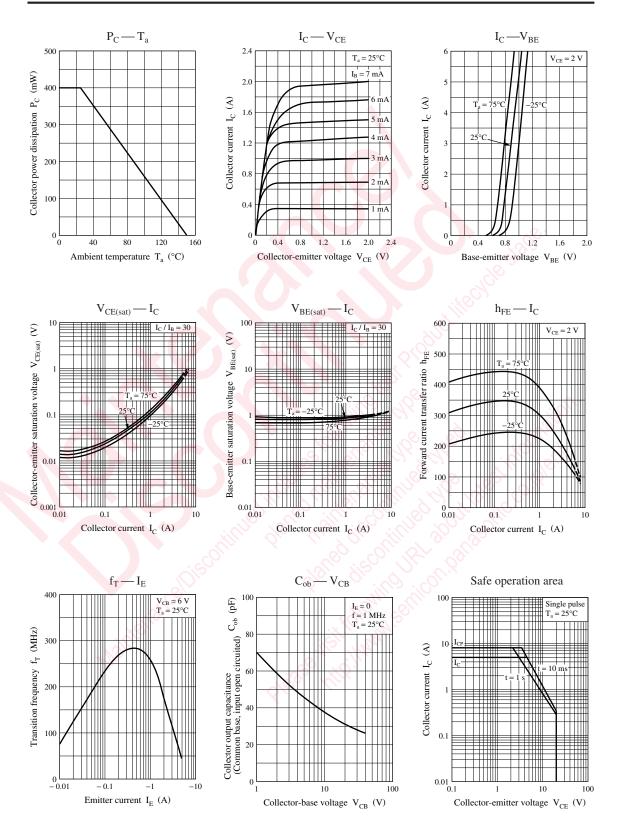
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$	20	SOL		V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_{\rm E} = 10 \ \mu A, I_{\rm C} = 0$	7	0-		V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 10 \text{ V}, I_E = 0$	2.		0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CB} = 10 \text{ V}, I_B = 0$			1	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = 7 V, I_C = 0$			0.1	μΑ
Forward current transfer ratio	h <sub>FE1</sub> *	$V_{CE} = 2 V, I_C = 0.5 A$	230		600	
	h <sub>FE2</sub>	$V_{CE} = 2 V, I_C = 2 A$	150			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 3 \text{ A}, I_{\rm B} = 0.1 \text{ A}$		0.28	1.00	V
Transition frequency	f <sub>T</sub>	$V_{CB} = 6 V, I_E = -50 mA, f = 200 MHz$		150		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = 20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		26	50	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Rank classification

Rank	Q	R
h <sub>FE1</sub>	230 to 380	340 to 600

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